

EXPEDITED PROCEDURE
UNDER 37 C.F.R. §1.116

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Naoki SHIBATA et al.

Serial No.: 09/885,046

Filed: June 21, 2001

Already entered
Group Art Unit: 2811

Examiner: Shouxiang Hu

For: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE AND
METHOD FOR PRODUCING THE SAME

Honorable Commissioner of Patents
Washington, D.C. 20231
Box AF

AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the Office Action dated October 24, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1, 2, 4, 5, 7, 32 and 33 as follows:

1. (Twice Amended) A group III nitride compound semiconductor device,
comprising:

a substrate having an upper surface;

an undercoat layer formed directly on an entirety of said upper surface of said
substrate, in which an upper surface of said undercoat layer is covered with convex portions,
each of said convex portions being shaped like a truncated hexagonal pyramid; and

group III nitride compound semiconductor layers formed on said undercoat
layer and having a device function.

2. (Amended) A group III nitride compound semiconductor device according to
claim 1, wherein said undercoat layer comprises GaN doped with magnesium.